

09/5/2009

ABSTRACT OF THE DISCLOSURE

The invention comprises integrated circuitry and to methods of forming capacitors. In one implementation, integrated circuitry includes a capacitor having a first capacitor electrode, a second capacitor electrode and a high K capacitor dielectric region received therebetween. The high K capacitor dielectric region has a high K substantially amorphous material layer and a high K substantially crystalline material layer. In one implementation, a capacitor forming method includes forming a first capacitor electrode layer over a substrate. A substantially amorphous first high K capacitor dielectric material layer is deposited over the first capacitor electrode layer. The substantially amorphous high K first capacitor dielectric material layer is converted to be substantially crystalline. After the converting, a substantially amorphous second high K capacitor dielectric material layer is deposited over the substantially crystalline first high K capacitor dielectric material layer. A second capacitor electrode layer is formed over the substantially amorphous second high K capacitor dielectric material layer.